IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A process of reforming a quartz glass crucible, wherein the quartz glass crucible is reformed by an arc discharge generated by electrodes positioned around a rotational axis and configured to heat an inside surface of the crucible while the crucible is rotated, the process comprising:

using an electrode structure having 3n electrodes with 3-phase alternating electric current, n being equal to or larger than 2, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration so as to form a stable ring-like arc between the neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration;

heating the inside surface of the crucible while the crucible is rotated, wherein a diameter of the crucible is 28 inches or more, and a radius r of the ring-like configuration around the rotational axis is at least ¼ of a radius R of an open portion of the crucible, but not greater than R, for at least a fixed time during arc heating; and

removing one of a foreign substance located on the inside surface and a bubble located under the inside surface by arc discharge.

2. (Previously Presented) The process of claim 1, wherein the using step comprises: arranging the electrodes in the electrode structure such that the neighboring electrodes are positioned at regular intervals in the ring-like configuration so as to have an absolute value θ of a phase difference of the alternating electric current in the range of $90^{\circ} \le \theta \le 180^{\circ}$.

3. (Canceled)

- 4. (Original) The process of claim 1, wherein a diameter of the crucible is 28 to 40 inches.
- 5. (Original) The process of claim 1, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.
- 6. (Original) The process of claim 2, wherein a diameter of the crucible is 28 to 40 inches.
- 7. (Original) The process of claim 2, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.
 - 8. (Canceled)
- 9. (Currently Amended) The process of claim [[8]] 2, wherein a diameter of the crucible is 28 to 40 inches.
- 10. (Currently Amended) The process of claim [[8]] 2, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.
- 11. (Original) The process of claim 3, wherein a diameter of the crucible is 28 to 40 inches.
- 12. (Original) The process of claim 3, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

13. (Currently Amended) A process of reforming a quartz glass crucible, comprising:

one of mechanically removing a foreign substance on an inside surface of the crucible and removing a bubble just under the inside surface of the crucible by grinding;

using an electrode structure having 3n electrodes with 3-phase alternating electric current, n being equal to or larger than 2, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration so as to form a ring-like arc between neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration, wherein a diameter of the crucible is 28 inches or more, and a radius r of the ring-like configuration around the rotational axis is at least ½ of a radius R of an open portion of the crucible, but not greater than R, for at least a fixed time during arc heating; and

fusing the inside surface of the crucible to be smoothed.

- 14. (Original) The process of claim 13, wherein a diameter of the crucible is 28 to 40 inches.
- 15. (Previously Presented) The process of claim 13, wherein the quartz glass crucible is used for the pulling up of single crystal silicon.

16-17. (Canceled)

18. (Currently Amended) A process of reforming a quartz glass crucible, wherein the quartz glass crucible is reformed by an arc discharge generated by electrodes positioned

around a rotational axis and configured to heat an inside surface of the crucible while the crucible is rotated, the process comprising:

using an electrode structure having 2n electrodes with 2-phase alternating electric current, n being equal to or larger than 2, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration so as to form a stable ring-like arc between the neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration;

heating the inside surface of the crucible while the crucible is rotated, wherein a diameter of the crucible is 28 inches or more, and a radius r of the ring-like configuration around the rotational axis is at least ¼ of a radius R of an open portion of the crucible, but not greater than R, for at least a fixed time during arc heating; and

removing one of a foreign substance located on the inside surface and a bubble located under the inside surface by arc discharge.

19. (Currently Amended) A process of reforming a quartz glass crucible, wherein the quartz glass crucible is reformed by an arc discharge generated by electrodes positioned around a rotational axis and configured to heat an inside surface of the crucible while the crucible is rotated, the process comprising:

using an electrode structure having 8 electrodes with 4-phase alternating electric current, wherein neighboring electrodes are positioned at regular intervals from each other in a ring-like configuration so as to form a stable ring-like arc between the neighboring electrodes, without generating a continuous arc between electrodes facing each other across a central portion of the ring-like configuration

heating the inside surface of the crucible while the crucible is rotated, wherein a diameter of the crucible is 28 inches or more, and a radius r of the ring-like configuration

around the rotational axis is at least ¼ of a radius R of an open portion of the crucible, but not grater than R, for at least a fixed time during arc heating; and

removing one of a foreign substance located on the inside surface and a bubble located under the inside surface by arc discharge.

20. (New) The process of claim 1, wherein the radius r is at least $\frac{1}{2}$ of the radius R.